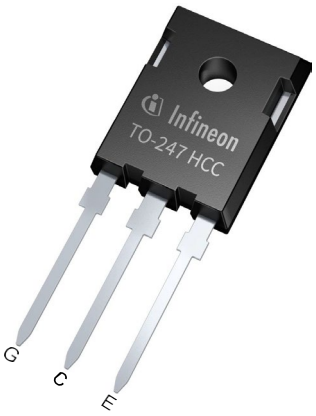
英飞凌IKWH30N65WR6

采用增强型爬电距离和电气间隙封装的 **TRENCHSTOP™ 5 WR6** 技术

英飞凌TRENCHSTOP™ 5 WR6 技术采用增强型爬电距离和电气间隙封装，提高了抗封装污染的可靠性

特性

- V_{CE} = 650 V
- I_C = 30 A
- 引脚间爬电距离 > 4.8 毫米
- 引脚间电气间隙 > 3.4 毫米
- 针对 PFC 和焊接应用进行优化的集成二极管
- 稳定的温度特性
- 极低的 V_{CEsat}和低的 E_{off}
- 基于 V_{CEsat}正温度系提升易于并联的能力
- V_{CEsat} 和 E_{sw}的温度依赖性
- 完整的产品范围和 PSpice 模型： http://www.infineon.com/igbt/



Lead-free

Green

Halogen-free

RoHS

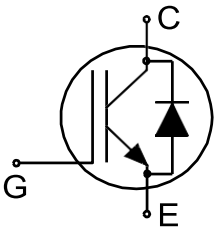
潜在应用

- 功率因数校正
- 焊接
- ZCS应用

产品验证

- 符合JEDEC47/20/22相关测试的工业应用要求

描述



Type	Package	Marking
IKWH30N65WR6	PG-TO247-3-STD-NN4.8	H30EWR6

目录

1 封装

表1 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Internal emitter inductance measured 5 mm (0.197 in.) from case	L_E			13		nH
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}	wave soldering 1.6 mm (0.063 in.) from case for 10 s			260	°C
Mounting torque	M	M3 screw, Maximum of mounting process: 3			0.6	Nm
Thermal resistance, junction-ambient	$R_{th(j-a)}$				40	K/W
IGBT thermal resistance, junction-case	$R_{th(j-c)}$				0.9	K/W
Diode thermal resistance, junction-case	$R_{th(j-c)}$				4.2	K/W

2 绝缘栅双极晶体管

表2 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Collector-emitter voltage	V_{CE}	$T_{vj} \geq 25$ °C		650	V
DC collector current, limited by T_{vjmax}	I_C		$T_c = 25$ °C	67	A
			$T_c = 100$ °C	42	
Pulsed collector current, t_p limited by T_{vjmax}	I_{Cpulse}			90	A
Turn-off safe operating area		$V_{CE} \leq 650$ V, $T_{vj} \leq 175$ °C		90	A
Gate-emitter voltage	V_{GE}			±20	V
Transient gate-emitter voltage	V_{GE}	$t_p \leq 10$ µs, $D < 0.01$		±30	V
Power dissipation	P_{tot}		$T_c = 25$ °C	165	W
			$T_c = 100$ °C	83	

表3 特征值

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Collector-emitter breakdown voltage	V_{BRCES}	$I_C = 0.2$ mA, $V_{GE}=0$ V	650			V

（表格续下页……）

表 3　　（续） 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Collector-emitter saturation voltage	V_{CEsat}	I_C = 30 A, V_{GE} = 15 V	T_{vj} = 25 °C		1.45	1.75	V
			T_{vj} = 175 °C		1.7		
Gate-emitter threshold voltage	V_{GEth}	I_C = 0.3 mA, V_{CE} = V_{GE}		3.2	4	4.8	V
Zero gate-voltage collector current	I_{CES}	V_{CE} = 650 V, V_{GE}=0 V	T_{vj} = 25 °C			40	µA
			T_{vj} = 175 °C		0.5		mA
Gate-emitter leakage current	I_{GES}	V_{CE}=0 V, V_{GE} = 20 V				100	nA
Transconductance	g_{fs}	I_C = 30 A, V_{CE} = 20 V			75		S
Input capacitance	C_{ies}	V_{CE} = 25 V, V_{GE}=0 V, f = 100 kHz			2700		pF
Output capacitance	C_{oes}	V_{CE} = 25 V, V_{GE}=0 V, f = 100 kHz			27		pF
Reverse transfer capacitance	C_{res}	V_{CE} = 25 V, V_{GE}=0 V, f = 100 kHz			11		pF
Gate charge	Q_G	I_C = 30 A, V_{GE} = 15 V, V_{CC} = 520 V			111		nC
Turn-on delay time	$t_{d(on)}$	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		35		ns
			T_{vj} = 175 °C, I_C = 30 A		31		
Rise time (inductive load)	t_r	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		18		ns
			T_{vj} = 175 °C, I_C = 30 A		20		
Turn-off delay time	$t_{d(off)}$	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		334		ns
			T_{vj} = 175 °C, I_C = 30 A		375		
Fall time (inductive load)	t_f	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		16		ns
			T_{vj} = 175 °C, I_C = 30 A		16		
Turn-on energy	E_{on}	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		0.82		mJ
			T_{vj} = 175 °C, I_C = 30 A		0.92		

（表格续下页……）

表 3 （续） 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Turn-off energy	E_{off}	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		0.38		mJ
			T_{vj} = 175 °C, I_C = 30 A		0.63		
Total switching energy	E_{ts}	V_{CC} = 400 V, V_{GE} = 0/15 V, $R_{G(on)}$ = 27 Ω, $R_{G(off)}$ = 27 Ω, L_σ = 30 nH, C_σ = 23 pF	T_{vj} = 25 °C, I_C = 30 A		1.2		mJ
			T_{vj} = 175 °C, I_C = 30 A		1.55		
Operating junction temperature	T_{vj}			-40		175	°C

除非另有规定，*电气特性均为 T_{vj} = 25°C。*

3 二极管

表4 最大额定值

Parameter	Symbol	Note or test condition		Values	Unit
Repetitive peak reverse voltage	V_{RRM}	T_{vj} ≥ 25 °C		650	V
Diode forward current, limited by T_{vjmax}	I_F		T_c = 25 °C	20	A
			T_c = 100 °C	11	
Diode pulsed current, t_p limited by T_{vjmax}	I_{Fpulse}			30	A

表5 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode forward voltage	V_F	I_F = 10 A	T_{vj} = 25 °C		1.3	1.6	V
			T_{vj} = 175 °C		1.35		
Diode reverse recovery time	t_{rr}	V_R = 400 V	T_{vj} = 25 °C, I_F = 15 A, $-di_F/dt$ = 1460 A/µs		82		ns
			T_{vj} = 175 °C, I_F = 15 A, $-di_F/dt$ = 1400 A/µs		94		

（表格续下页……）

表 5 （续） 特征值

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Diode reverse recovery charge	Q_{rr}	V_R = 400 V	T_{vj} = 25 °C, I_F = 15 A, $-di_F/dt$ = 1460 A/µs		1.4		µC
			T_{vj} = 175 °C, I_F = 15 A, $-di_F/dt$ = 1400 A/µs		2.2		
Diode peak reverse recovery current	I_{rrm}	V_R = 400 V	T_{vj} = 25 °C, I_F = 15 A, $-di_F/dt$ = 1460 A/µs		24		A
			T_{vj} = 175 °C, I_F = 15 A, $-di_F/dt$ = 1400 A/µs		28.8		
Diode peak rate of fall of reverse recovery current	di_{rr}/dt	V_R = 400 V	T_{vj} = 25 °C, I_F = 15 A, $-di_F/dt$ = 1460 A/µs		700		A/µs
			T_{vj} = 175 °C, I_F = 15 A, $-di_F/dt$ = 1400 A/µs		830		
Operating junction temperature	T_{vj}			-40		175	°C

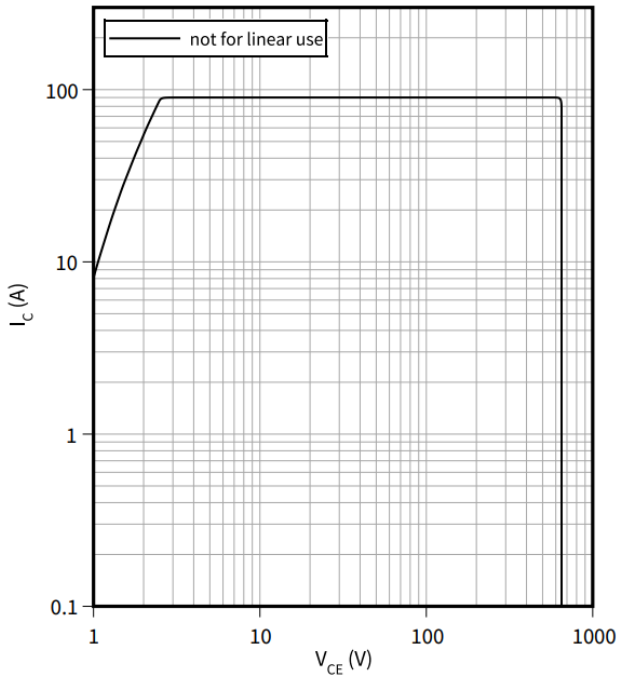
注意：为了获得最佳的使用寿命和可靠性，英飞凌建议运行条件不超过本数据手册中所述最大额定值的80%。

4 特性图

Reverse bias safe operating area

$I_C = f(V_{CE})$

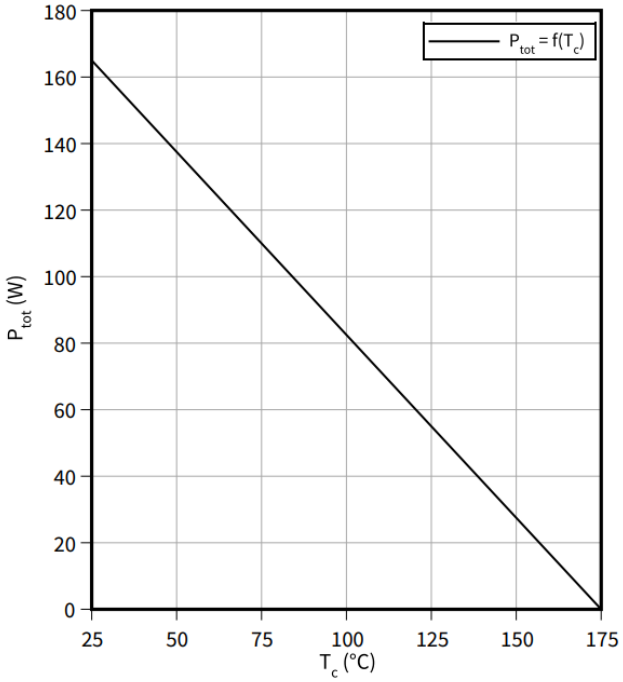
$T_{vj} \leq 175\ °C$, $T_c = 25\ °C$, $V_{GE} = 15\ V$



Power dissipation as a function of case temperature

$P_{tot} = f(T_c)$

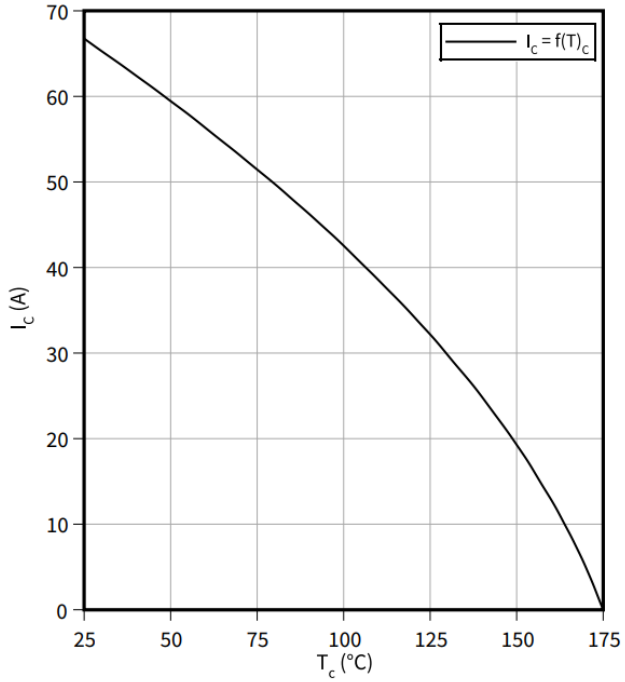
$T_{vj} \leq 175\ °C$



Collector current as a function of case temperature

$I_C = f(T_c)$

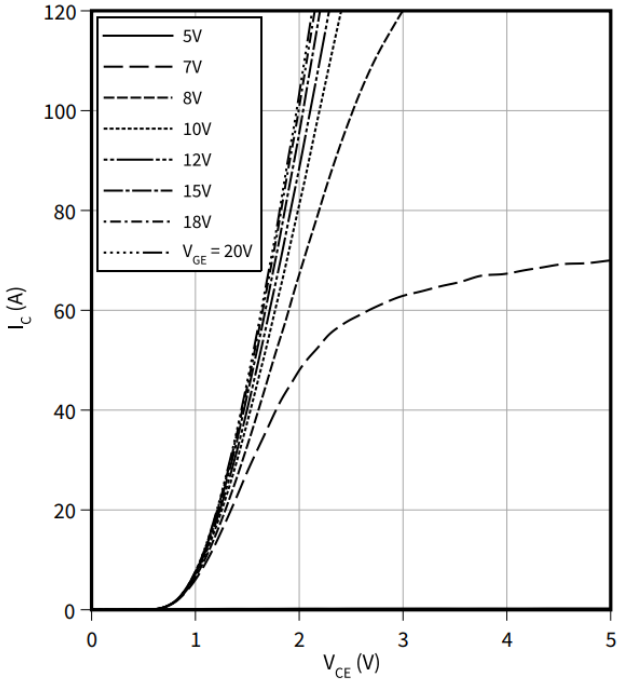
$T_{vj} \leq 175\ °C$, $V_{GE} \geq 15\ V$



Typical output characteristic

$I_C = f(V_{CE})$

$T_{vj} = 25\ °C$

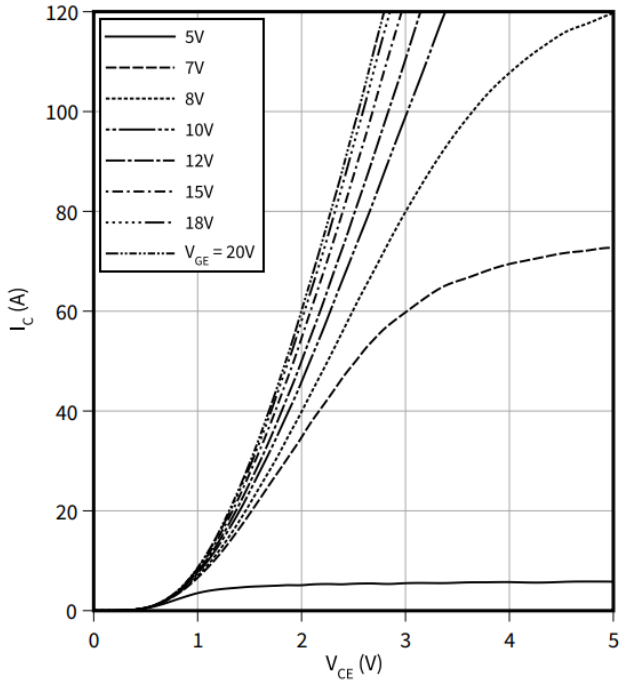


4 特性图

Typical output characteristic

$I_C = f(V_{CE})$

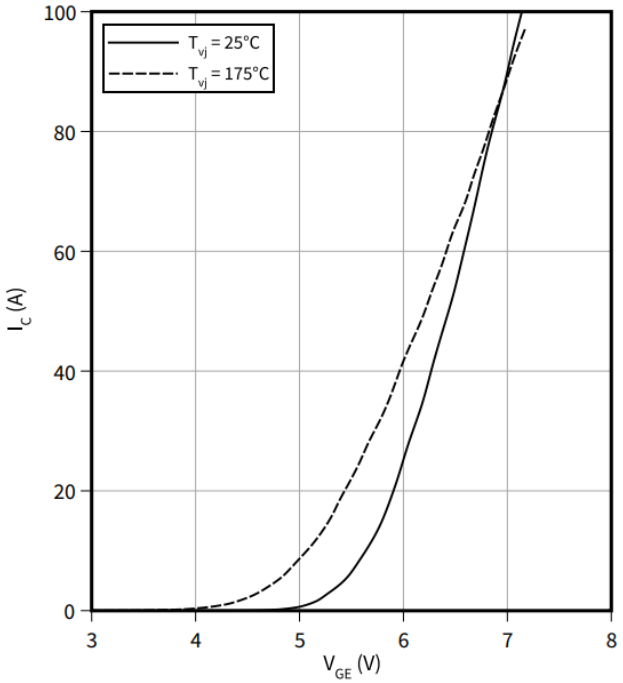
$T_{vj} = 175\ °C$



Typical transfer characteristic

$I_C = f(V_{GE})$

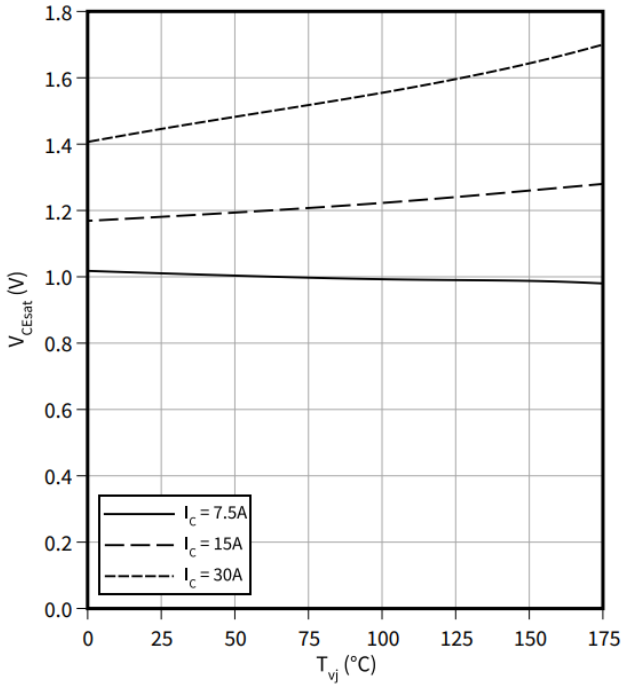
$V_{CE} = 20\ V$



Typical collector-emitter saturation voltage as a function of junction temperature

$V_{CEsat} = f(T_{vj})$

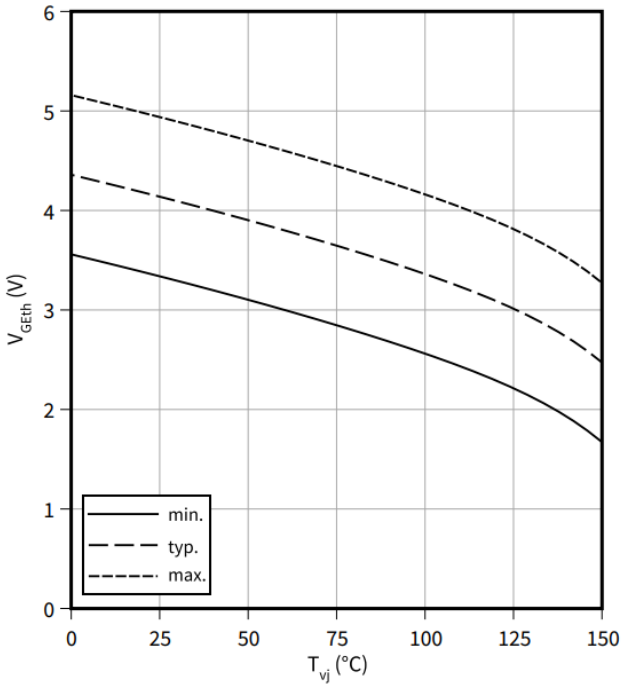
$V_{GE} = 15\ V$



Gate-emitter threshold voltage as a function of junction temperature

$V_{GEth} = f(T_{vj})$

$I_C = 0.3\ mA$

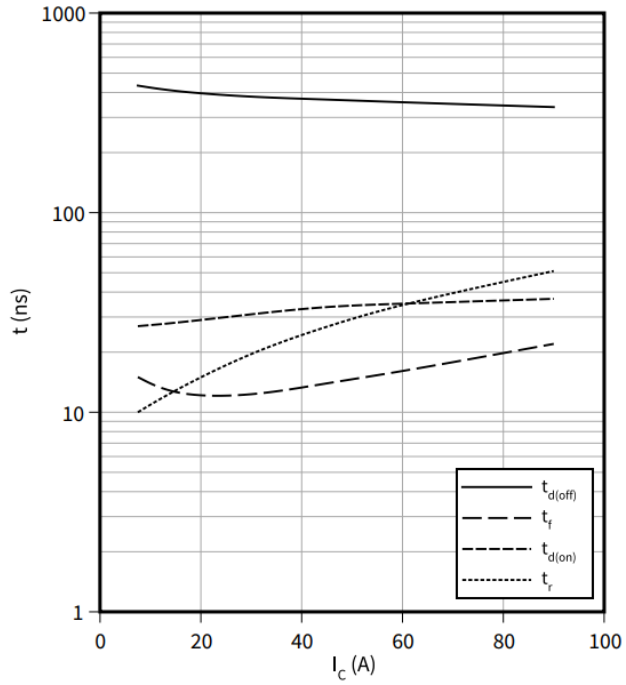


4 特性图

Typical switching times as a function of collector current

$t = f(I_C)$

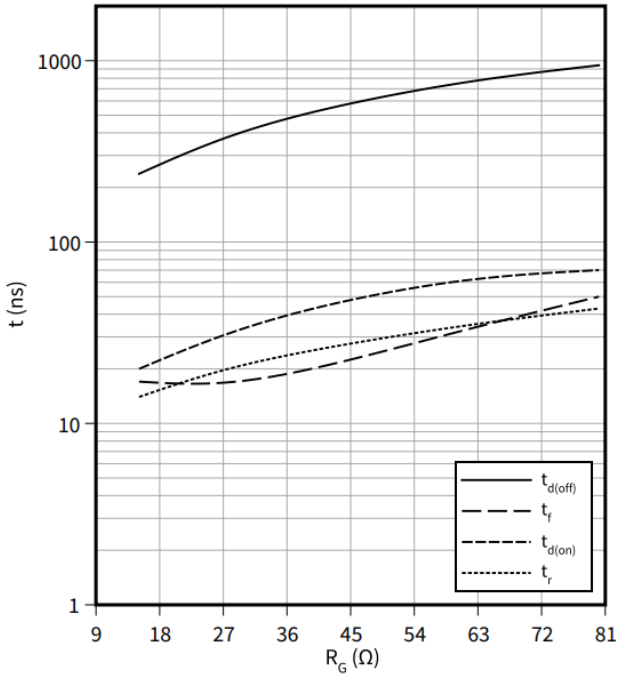
V_{CC} = 400 V, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 27 Ω



Typical switching times as a function of gate resistor

$t = f(R_G)$

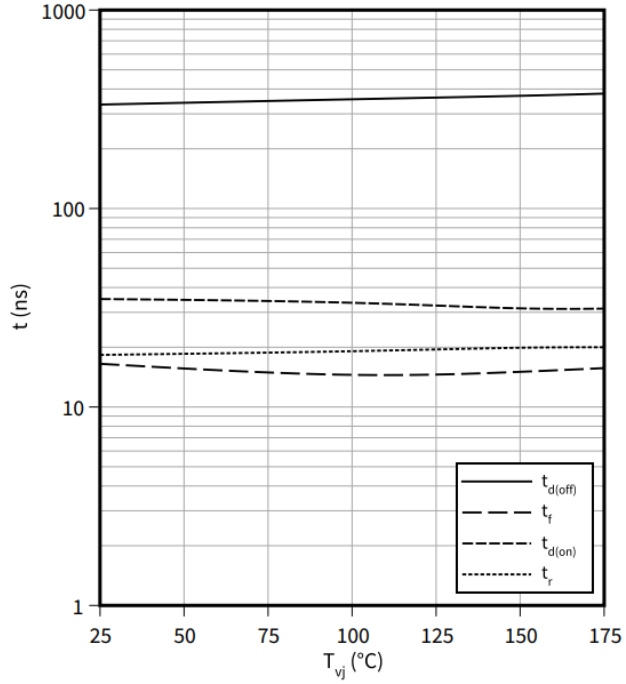
I_C = 30 A, V_{CC} = 400 V, T_{vj} = 175 °C, V_{GE} = 0/15 V



Typical switching times as a function of junction temperature

$t = f(T_{vj})$

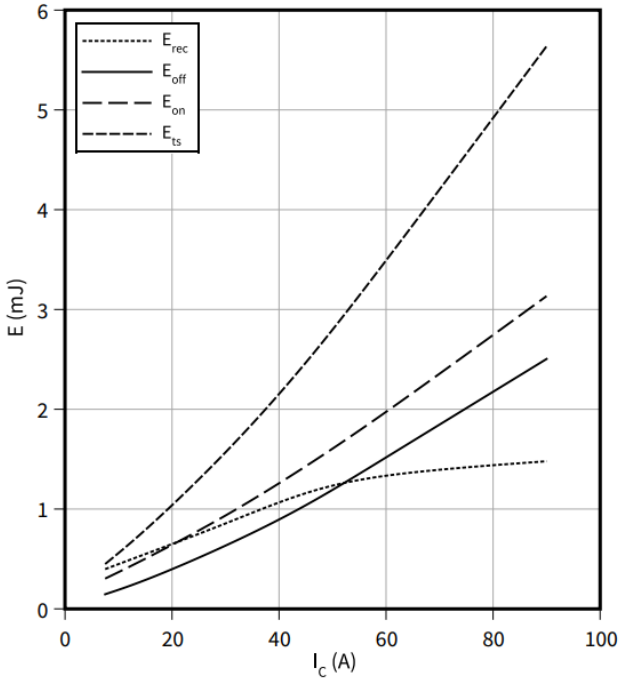
I_C = 30 A, V_{CC} = 400 V, V_{GE} = 0/15 V, R_G = 27 Ω



Typical switching energy losses as a function of collector current

$E = f(I_C)$

V_{CC} = 400 V, T_{vj} = 175 °C, V_{GE} = 0/15 V, R_G = 27 Ω

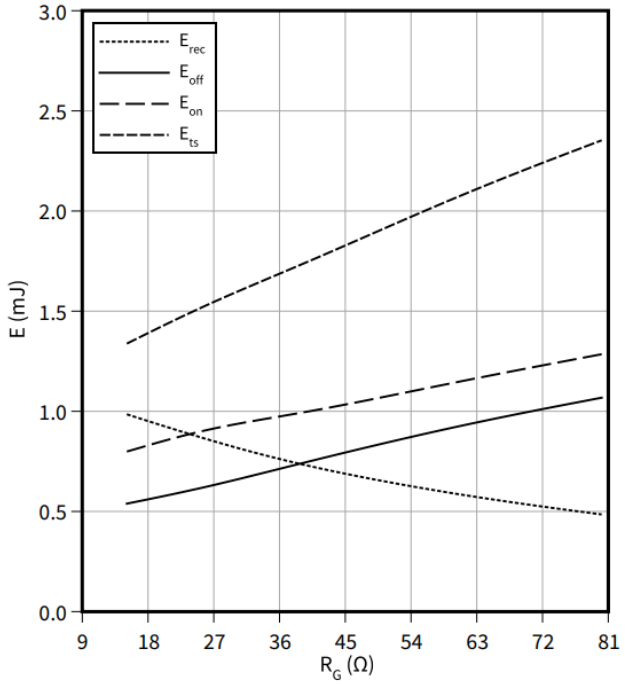


4 特性图

Typical switching energy losses as a function of gate resistor

$E = f(R_G)$

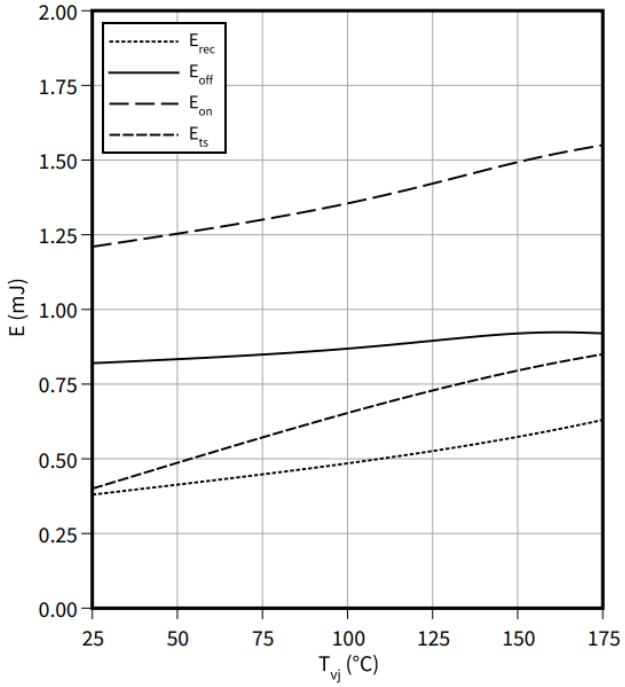
$I_C = 30\ A$, $V_{CC} = 400\ V$, $T_{vj} = 175\ °C$, $V_{GE} = 0/15\ V$



Typical switching energy losses as a function of junction temperature

$E = f(T_{vj})$

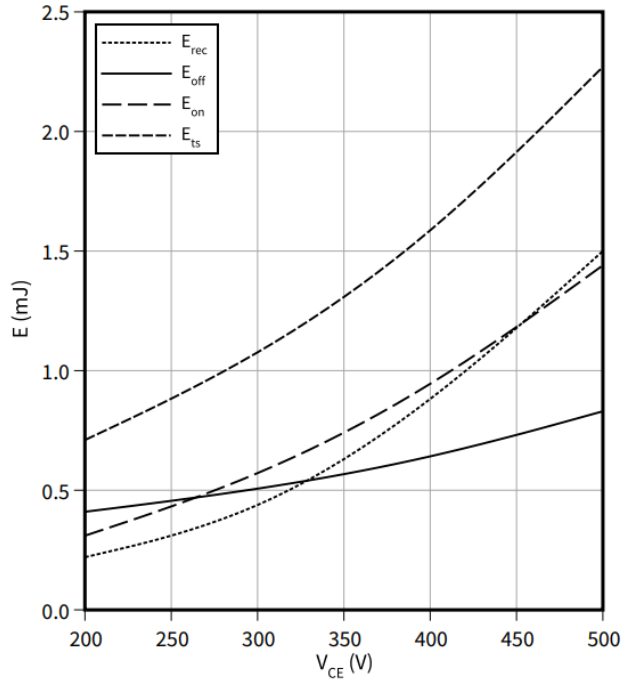
$I_C = 30\ A$, $V_{CC} = 400\ V$, $V_{GE} = 0/15\ V$, $R_G = 27\ Ω$



Typical switching energy losses as a function of collector emitter voltage

$E = f(V_{CE})$

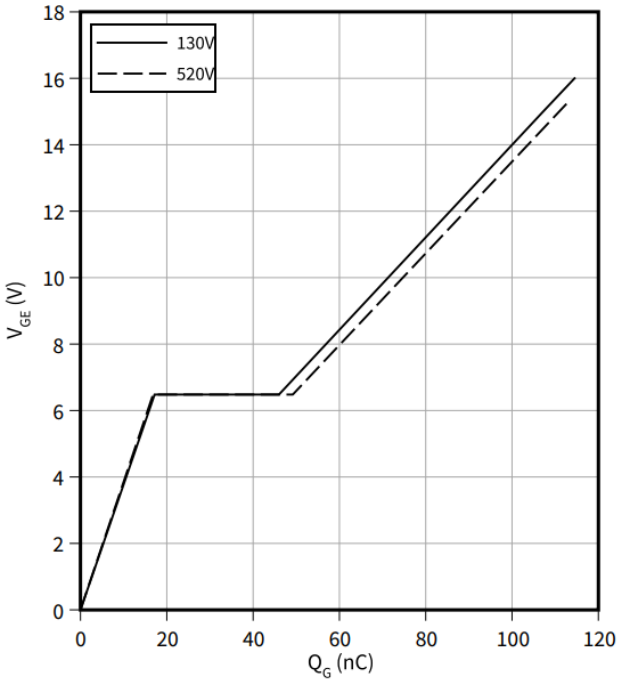
$I_C = 30\ A$, $T_{vj} = 175\ °C$, $V_{GE} = 0/15\ V$, $R_G = 27\ Ω$



Typical gate charge

$V_{GE} = f(Q_G)$

$I_C = 30\ A$

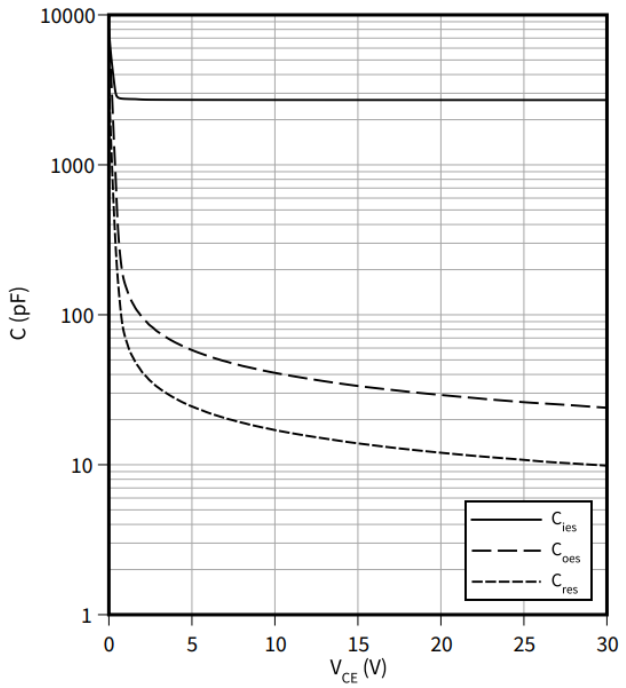


4 特性图

Typical capacitance as a function of collector-emitter voltage

$C = f(V_{CE})$

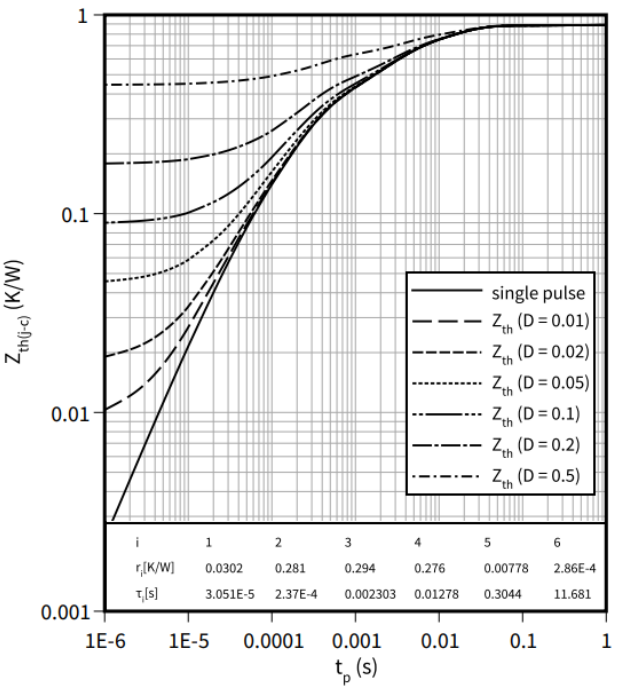
$f = 100\ kHz, V_{GE} = 0\ V$



IGBT transient thermal impedance as a function of pulse width

$Z_{th(j-c)} = f(t_p)$

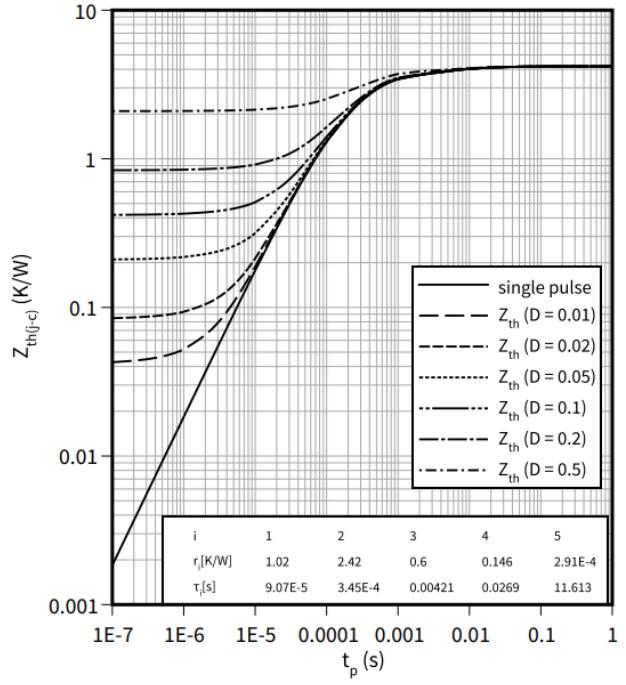
$D = t_p/T$



Diode transient thermal impedance as a function of pulse width

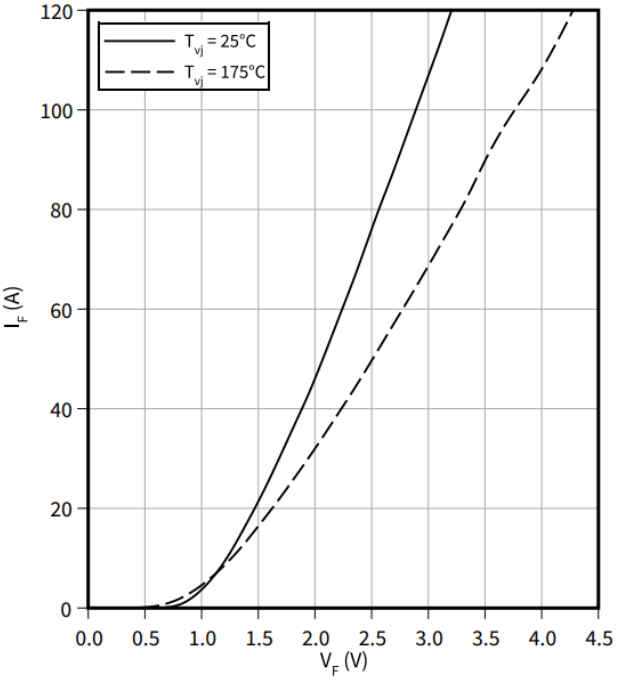
$Z_{th(j-c)} = f(t_p)$

$D = t_p/T$



Typical diode forward current as a function of forward voltage

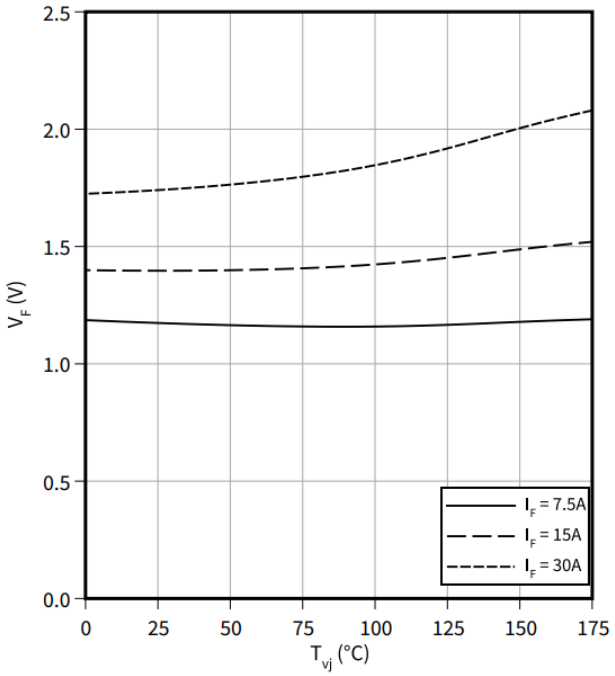
$I_F = f(V_F)$



4 特性图

Typical diode forward voltage as a function of junction temperature

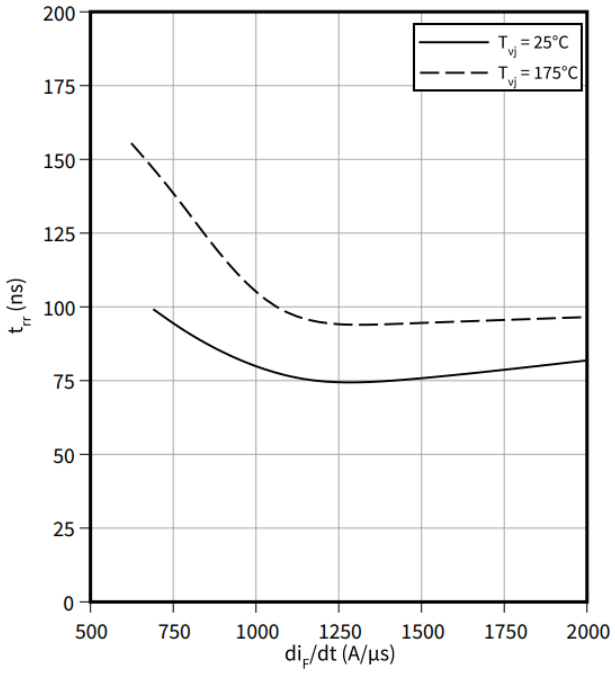
$V_F = f(T_{vj})$



Typical reverse recovery time as a function of diode current slope

$t_{rr} = f(di_F/dt)$

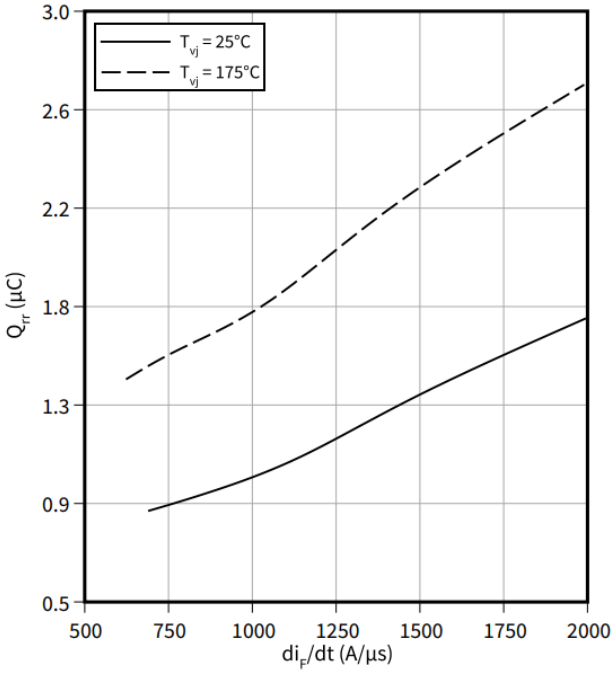
$V_R = 400\ V,\ I_F = 15\ A$



Typical reverse recovery charge as a function of diode current slope

$Q_{rr} = f(di_F/dt)$

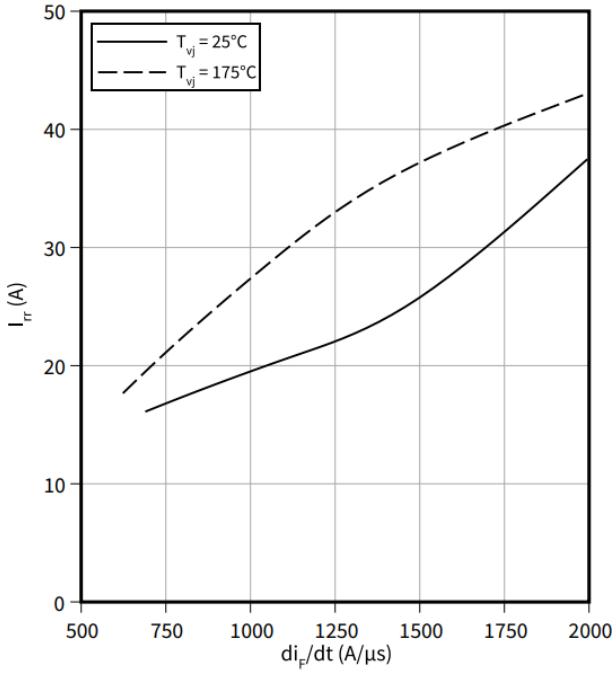
$V_R = 400\ V,\ I_F = 15\ A$



Typical reverse recovery current as a function of diode current slope

$I_{rrm} = f(di_F/dt)$

$V_R = 400\ V,\ I_F = 15\ A$

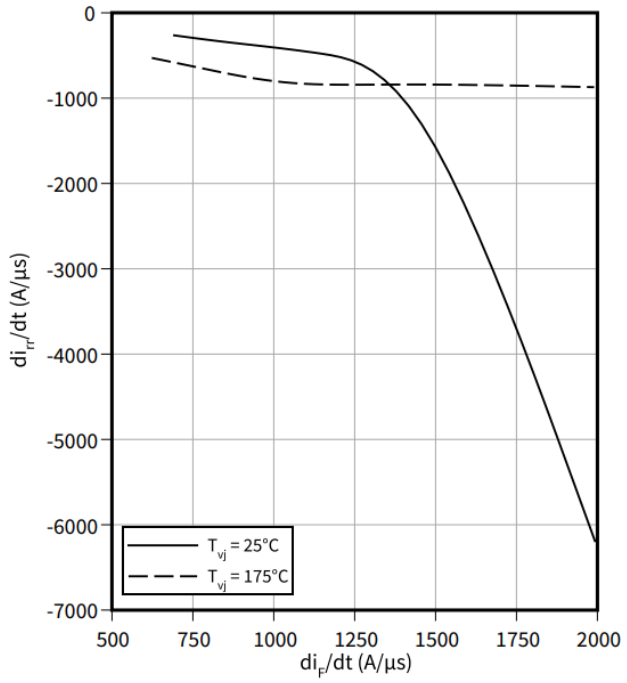


4 特性图

Typical diode peak rate of fall of reverse recovery current as a function of diode current slope

$di_{rr}/dt = f(di_F/dt)$

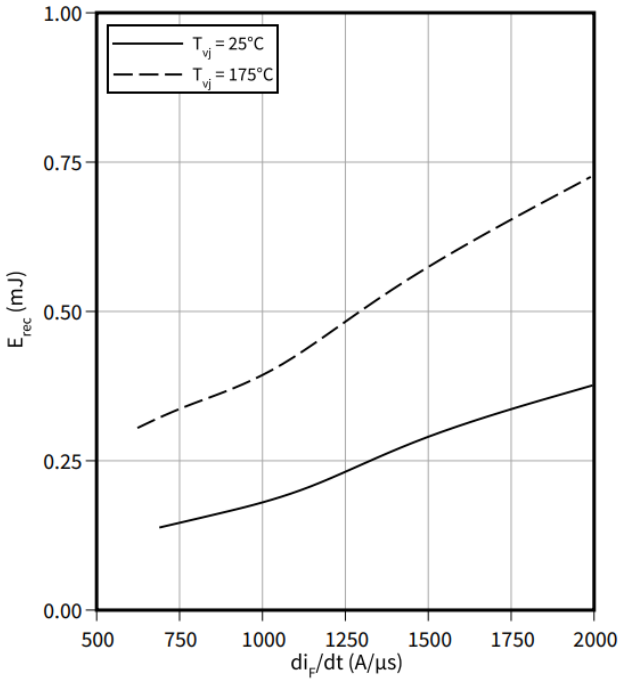
$V_R = 400\ V$, $I_F = 15\ A$



Typical reverse energy losses as a function of diode current slope

$E_{rec} = f(di_F/dt)$

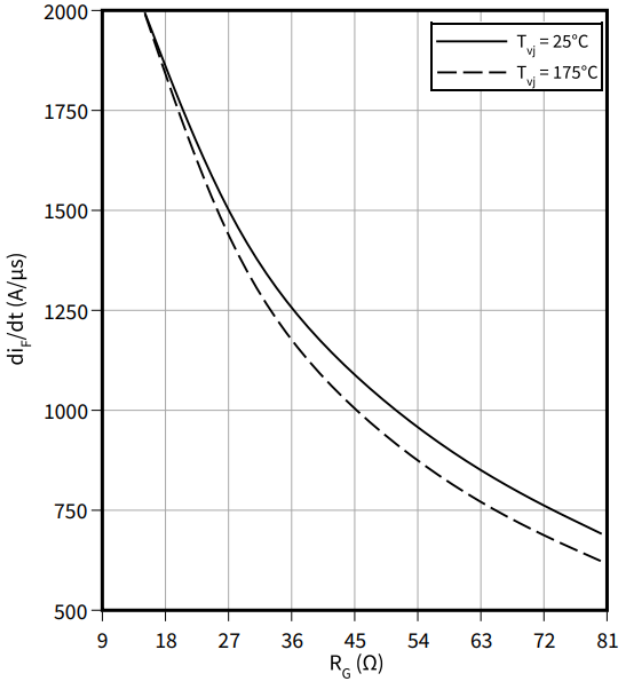
$V_R = 400\ V$, $I_F = 15\ A$



Typical diode current slope as a function of gate resistor

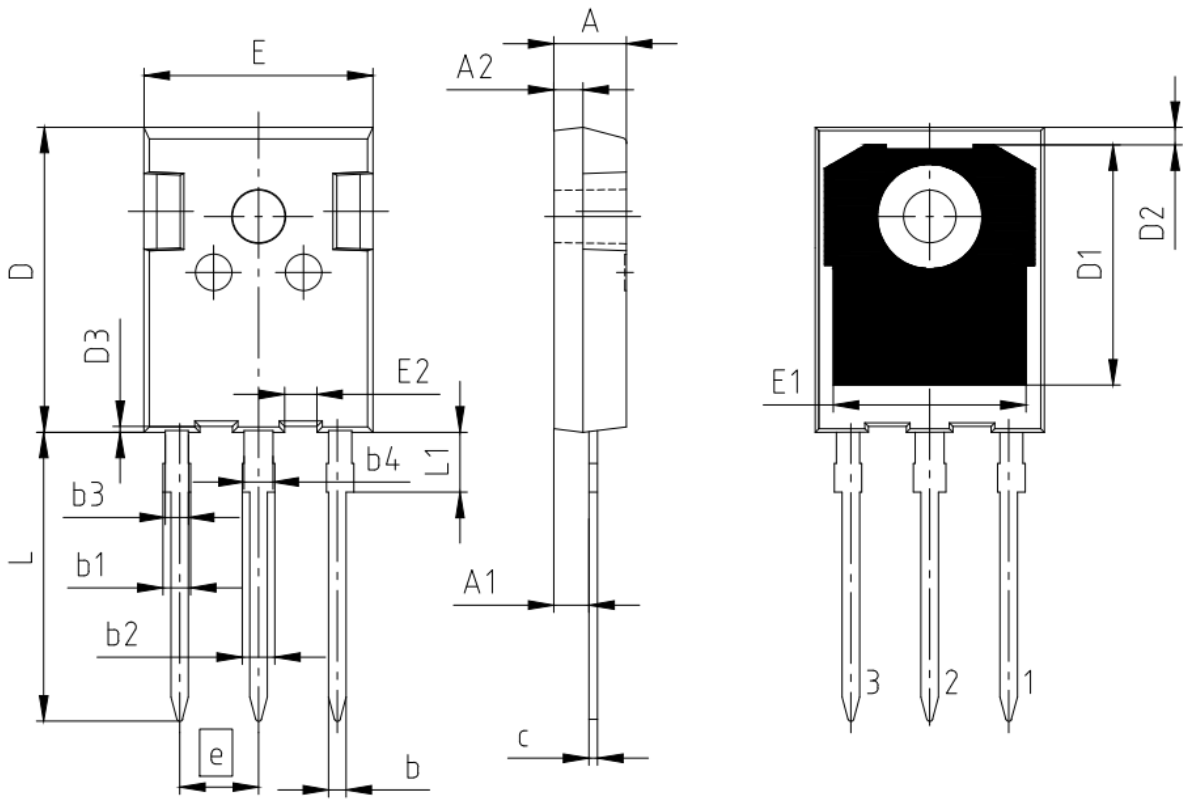
$di_F/dt = f(R_G)$

$V_R = 400\ V$, $I_F = 15\ A$



5 封装外形

PG-TO247-3-STD-NN4.8



PACKAGE - GROUP NUMBER:	PG-TO247-3-U04	
DIMENSIONS	**MILLIMETERS**	
	MIN.	MAX.
A	4.90	5.10
A1	2.31	2.51
A2	1.90	2.10
b	1.16	1.26
b1		1.90
b2		2.30
b3	1.55	1.65
b4	1.96	2.06
c	0.59	0.66
D	20.90	21.10
D1	16.25	16.85
D2	1.05	1.35
D3	0.55	0.65
E	15.70	15.90
E1	13.10	13.50
E2	2.14	2.34
e	5.44	
N	3	
L	19.80	20.10
L1	3.95	4.30

图 1

6 测试条件

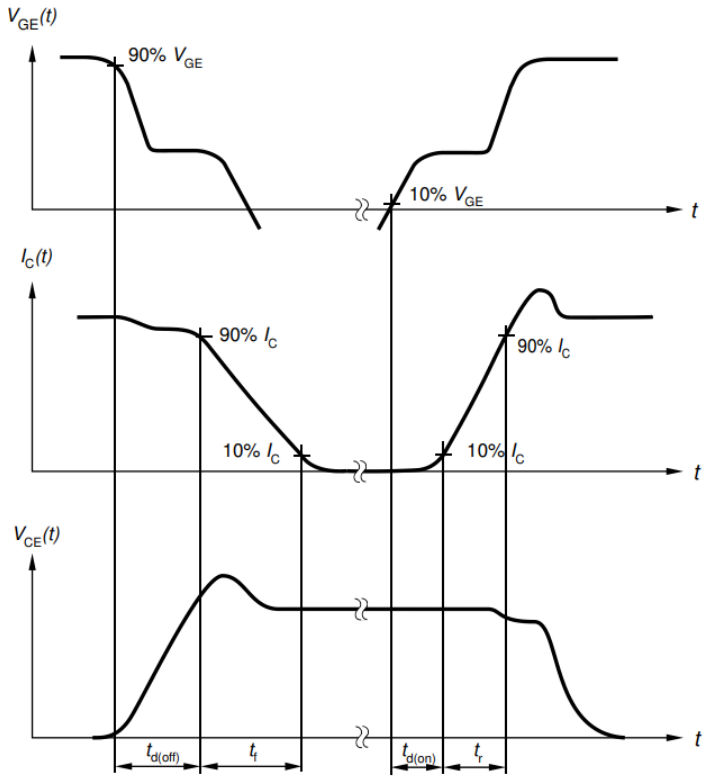


Figure A. **Definition of switching times**

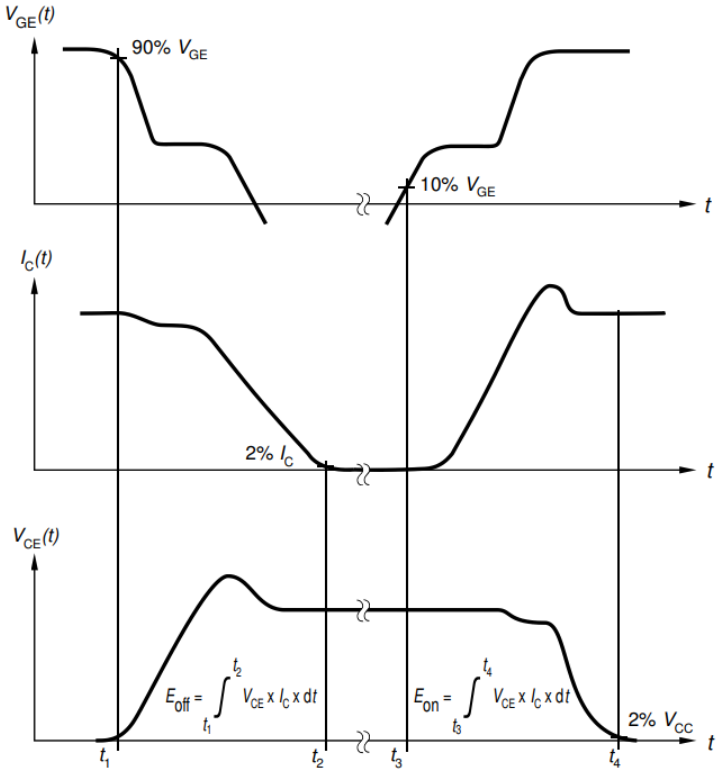


Figure B. **Definition of switching losses**

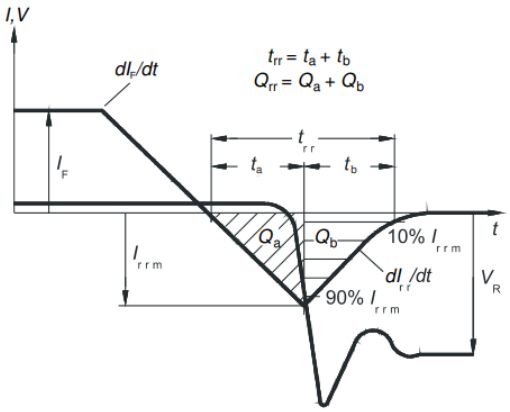


Figure C. **Definition of diode switching characteristics**

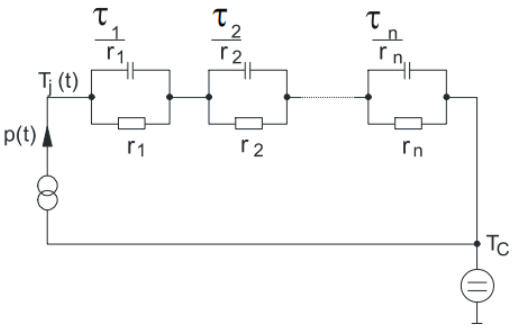


Figure D. **Thermal equivalent circuit**

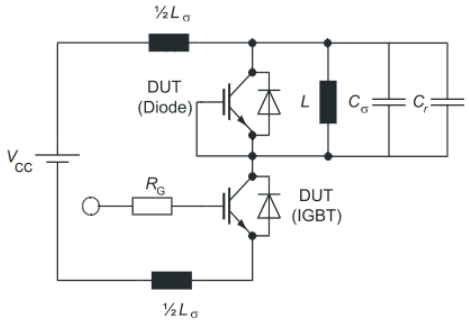


Figure E. **Dynamic test circuit**
Parasitic inductance L_σ,
parasitic capacitor C_σ,
relief capacitor C_r,
(only for ZVT switching)

图 2

修订记录

Document revision	Date of release	Description of changes
1.00	2021-05-17	Final datasheet
1.10	2021-05-18	Update of diagram E = f(Tvj)
1.20	2021-06-29	Update of diagram E = f(T_{vj})
1.30	2022-12-06	Update of “DC collector current, limited by T_{vjmax}” in table “Maximum rated values”, for 25°C and 100°C Transient gate-emitter voltage V_{GE} in table “Maximum rated values” of IGBT changed to ±30V Update of diagram “Collector current as a function of case temperature”, $I_C = f(T_c)$ "Forward bias safe operating area” diagram renamed to “Reverse bias safe operating area” Correction of package outline dimensions Change package name to marketing name Editorial changes

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